

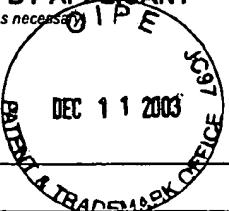
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PTO/SB/05A (10-01)

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	09/256643
		Filing Date	February 23, 1999
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2822
		Examiner Name	Trinh, Michael
		Sheet 1 of 2	
Attorney Docket No: 303.324US2			

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Substitute Disclosure Statement Form (PTO-1448)

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		Application Number	09/256643
		Filing Date	February 23, 1999
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2822
		Examiner Name	Trinh, Michael
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